Voltage control of domain walls in magnetic nanowires for energy efficient neuromorphic devices

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Abstract

An energy-efficient voltage controlled domain wall device for implementing an artificial neuron and synapse is analysed using micromagnetic modeling in the presence of room temperature thermal noise. By controlling the domain wall motion utilizing spin-orbit torque in association with voltage control of perpendicular magnetic anisotropy in the presence of Dzyaloshinskii-Moriya interaction, different positions of the domain wall are realized in the free layer of a magnetic tunnel junction to program different synaptic weights. Notches in the free layer are used to produce discrete positions of the domain wall. The feasibility of scaling of such devices is assessed in the presence of thermal perturbations that compromise controllability. Additionally, an artificial neuron can be realized by combining this DW device with a CMOS buffer. This provides a possible pathway to realize energy efficient voltage controlled nanomagnetic deep neural networks that can learn in real time.
I. Introduction

There has been considerable recent progress in the development of dedicated CMOS processors for neuromorphic computing such as IBM’s TrueNorth that can implement 1 million spiking neurons and 256 million configurable synapses [1] while consuming ~70mW power. However, these neuromorphic processors have drawbacks such as lack of onboard (real-time) learning/training. More importantly, they have poor energy efficiency in comparison to the human brain, which has ~ 100 billion neurons and ~ 500 trillion synapses and consumes a mere ~ 20 watts of power [2].

Thus, a key challenge for hardware implementation of artificial neural networks shown in Fig. 1 lies in finding energy efficient hardware implementations of neurons and non-volatile synapses whose weights can be changed easily and deterministically with very little energy as the network learns from data in real time. While artificial neurons and synapses have been proposed using current-controlled nanomagnets [3-9] and memristors [10-15] that are potentially more energy efficient than pure CMOS implementations, there is still room for increasing the energy efficiency.

Here we propose and comprehensively model the Domain Wall (DW) dynamics in magnetostrictive CoFeB nanowires that are clocked with Spin Orbit Torques (SOT) [16-20] in conjunction with an anisotropy gradient [21, 22]. Our scheme proposes to arrest the DW position at specific locations along the wire defined by notches. The DW is translated to specific notches in an energy efficient manner by SOT in combination with a voltage-induced strain that provides a variable gradient in perpendicular magnetic anisotropy (PMA). Such an implementation is important in applications where energy efficiency is at a premium, such as medical processors and sensor networks that need to learn from data in real time rather than be trained offline, and where synaptic weights of limited accuracy are sufficient [23].

In this paper, we examine the magnetization dynamics of the chiral Néel domain walls in a thin nanowire of CoFeB with PMA that is modulated by a voltage-induced strain. The CoFeB experiences a Dzyaloshinskii-Moriya Interaction (DMI) that stabilizes chiral walls [20], which are translated by SOT [24-27] to implement energy efficient non-volatile artificial synapses. We also describe the manner in which this device, in combination with a CMOS buffer, can also function as a neuron and implement Deep Neural Networks (DNNs). Section II describes the working principle of the device and our micromagnetic modeling approach. Section III presents and discusses simulation of the DW dynamics in the presence of PMA gradients and SOT while Section IV compares the energy efficiency of this approach with other spintronic and memristor approaches.
II. Device working principle and micromagnetic modeling approach

The working principle of the device (Fig. 1 below) is explained in terms of the DW dynamics within the magnetic free layer (here, CoFeB), of a magnetic tunnel junction (MTJ). The resistance of the MTJ, which consists of a free layer, a tunnel junction and a fixed layer pinned by a synthetic antiferromagnet (SAF), varies with the location of the DW in the free layer. The DW position determines the non-volatile resistance states of the spintronic synapse and can be programed by a voltage, as described below. As the Deep Neural Network (DNN) learns from data in real time, a backpropagation algorithm [28] implemented on a CMOS application-specific co-processor can calculate the new weights for different synapses and output these as specific programming voltages (not addressed in this paper). These voltages should be able to reprogram the resistance states of the synapses to update their resistance values, as described in this work.

**SOT clocking:** Consider a perpendicular magnetic anisotropy racetrack consisting of a Pt/CoFeB bilayer on a piezoelectric film as shown in the lower panel of Fig. 1(b). The ferromagnetic layer of a heavy metal/ferromagnetic metal bilayer (e.g. Pt/CoFeB) derives its PMA from interfacial effects [29] and exhibits significant Dzyaloshinskii-Moriya Interactions (DMI) that stabilize the formation of chiral Néel domain walls. Spin orbit torques (SOT) acting on the magnetization are generated when current flows in the Pt layer. The damping like field (DL-field) thus produced in these systems is responsible for translating the Neel domain wall in the CoFeB layer [29]. Reversing the direction of the current in the Pt layer reverses

![Fig. 1. Schematic of the spintronic DW-synapse. (a) Top view showing a magnetic tunnel junction (MTJ) stack placed adjacent to an electrode on a piezoelectric substrate. The inset shows the PMA as a function of distance along the free layer when a voltage is applied to the strain electrode. (b) Front view of the stack (top panel). In the bottom panel, which shows just the heavy metal/free layer, the electrons on the top surface of the Pt are spin polarized into the plane of the figure and electrons at the bottom are spin polarized out of the plane of the figure due to the spin Hall effect.](image)
the direction of domain wall motion, resets the domain wall position, and hence resets the resistance of the DW MTJ device.

**Voltage control of domain wall position:** Stopping the domain wall at a specific position along the racetrack is accomplished by the voltage applied to the side electrode (Fig 1(a)) while the DW is being “clocked” by spin orbit torque. Consider a domain wall that has been “reset” to one end of the racetrack and is moved along the racetrack towards the other end in Fig. 1 (a) by SOT from a current in the adjacent Pt layer. Application of a voltage between the side electrode and the bottom contact of the piezoelectric layer produces an electric field through the piezoelectric thickness, which in turn produces an in-plane stress in the manner of Ref [30]. This leads to a local strain gradient in the piezoelectric, which is transferred to the soft CoFeB layer, altering its PMA as shown in Fig. 1(a) (inset).

The mechanism of generation of the strain gradient is explained in detail in Fig. 2. When a voltage is applied to the top electrode, a local electric field is generated through the thickness of the PZT between the area directly underneath the top electrode area and the bottom electrode. This causes an out of plane expansion of the PZT and consequently an in-plane contraction (due to Poisson’s ratio) of the area below the top electrode. This produces a tensile in-plane strain in the region of the PZT immediately adjoining the electrode, with a magnitude that decreases with distance away from the electrode. This creates a strain gradient as shown in Fig. 2, upper schematic. While a similar strain gradient is created in the in-plane direction orthogonal to that shown in the figure, we are only concerned with the strain gradient along the DW MTJ device. Furthermore, if the PZT is deposited on a stiff substrate, the bottom of the PZT is clamped but the top part of the PZT can experience the in-plane strain gradient.

![Fig. 2. A schematic showing the strain gradient produced on the DW MTJ when a voltage is applied to the top strain electrode. The in-plane tensile strain decreases from the right end of the DW MTJ to the left producing a PMA gradient.](image)

The benefit of this scheme is that the piezoelectric film develops a strain gradient [30] even though it is not patterned provided the in-plane dimension of the electrode is approximately equal to the thickness of the film [30]. The strain gradient will be most significant within a distance of one to two times the
piezoelectric film thickness [30]. This in-plane strain in turn modulates the perpendicular anisotropy of the soft layer and provides a spatial variation of the energy landscape of the Neel DW in the CoFeB racetrack. Thus, the device relies on stress generated by the electrode to arrest the SOT-induced motion of the DW, leaving the DW pinned at a notch. The strain and therefore modulation of PMA is largest at the left end, and minimum at the right end (Fig 1(a)). This PMA gradient in conjunction with the SOT and geometrical arrangement of notches patterned in the wire determines the position where the DW is arrested.

**Micromagnetic model:** Mumax [31] was used to perform simulations of the domain wall dynamics using the Landau-Lifshitz-Gilbert (LLG) equation in the presence of thermal noise at room temperature. The time rate of change of magnetization in a volume element of the magnetic material is given by:

\[
\frac{d\vec{m}}{dt} = \vec{\tau} = \left(\frac{-\gamma}{1+\alpha^2}\right)\left(\vec{m} \times \vec{H}_{\text{eff}} + \alpha \left(\vec{m} \times (\vec{m} \times \vec{H}_{\text{eff}})\right)\right)
\]  

(3).

where \( \vec{m} \) is the reduced magnetization (\( \vec{M}/M_{\text{sat}} \)), \( M_{\text{sat}} \) is the saturation magnetization, \( \gamma \) is the gyromagnetic ratio and \( \alpha \) is the Gilbert damping coefficient. The quantity \( H_{\text{eff}} \) is the effective magnetic field, which is given by:

\[
H_{\text{eff}} = H_{\text{demag}} + H_{\text{exchange}} + H_{\text{anisotropy}} + H_{\text{thermal}}
\]  

(4).

Here, \( H_{\text{demag}} \) is the demagnetizing field produced by all the other volume elements of the magnetic material, and \( H_{\text{exchange}} \) is the effective field due to Heisenberg exchange coupling and DMI [32, 33]. The DMI contribution to the effective exchange field is given by:

\[
H_{\text{DM}} = \frac{2D}{\mu_0 M_{\text{sat}}} \left(\vec{\nabla} \cdot \vec{m}\right) - \vec{\nabla} m_z
\]  

(5).

where \( m_z \) is the \( z \)-component of magnetization and \( D \) is the effective DMI constant. The effective field due to the perpendicular anisotropy is

\[
H_{\text{anis}} = \frac{K_{u1}}{\mu_0 M_{\text{sat}}} (\vec{u} \cdot \vec{m}) \vec{u} + \frac{4K_{u2}}{\mu_0 M_{\text{sat}}} (\vec{u} \times \vec{m}) \times \vec{u}
\]  

(6).

where, \( K_{u1} \) and \( K_{u2} \) are first and second order uniaxial anisotropy constants respectively and \( \vec{u} \) is the unit vector in the out-of-plane (OP) direction. Strain effectively modulates the anisotropy energy and is incorporated by modulating \( K_{u1} \) according to Eq. (2). We assume \( K_{u2} = 0 \), as we are not dealing with textured or single crystal materials [34].
Thermal noise is modeled by a random, effective magnetic field \( H_{\text{thermal}} \) applied in the manner described in [35, 36] within a micromagnetic framework [31]. Furthermore, the field-like and damping-like SOTs are modeled with the appropriate terms [12].

The discretization cell sizes used for the simulations were 4\( \text{nm} \times 4\text{nm} \times 1\text{nm} \) for the 1000\( \text{nm} \times 100\text{nm} \times 1\text{nm} \) free layer and the material parameters used for CoFeB (soft layer) of the Pt/CoFeB/MgO heterostructure is summarized in Table 1.

### III. Discussion of modeling results

We discuss the modeling results for nanowires of length 1000 nm and width 100 nm patterned with five notches as shown in Fig 3. A gradient in PMA caused by the strain gradient drives the DW towards the lower PMA region in order to reduce the DW energy, i.e. motion is induced in the direction of the negative PMA gradient. We consider the case where the PMA gradient and the SOT drive the DW in the same direction, and then we perform simulation in the presence of thermal noise to understand if these DWs can be arrested deterministically at room temperature and understand scaling behavior of this device.

#### a. CoFeB soft layer dimension: 1000 nm \( \times \) 100 nm \( \times \) 1 nm: PMA gradient assists SOT-driven DW motion

In a MTJ racetrack with CoFeB soft layer, the DW motion was initiated by SOT assisted by a PMA gradient (without including the effect of thermal noise). Given that the SOT acts as the clocking signal, the ON time for SOT is fixed at 6 ns. This is considered the "write time" for reprogramming the synaptic weight and, based on the analysis of the DW motion at different SOT currents and PMA gradients, it is sufficient to translate the DW to any possible location within the device.
Table 2 shows the PMA gradients required to drive the DW from notch 1 to any of the other notches in Fig 3, if the current density of the SOT clock is kept constant at $4.35 \times 10^{13}$ $A/m^2$, which is just below the critical current needed to de-pin and initiate the DW motion. For a Pt layer of 1 nm thickness and width 50 nm this corresponds to a current of ~2 mA. We do not account for increase in current density at the notches in this simulation, which corresponds to the case that the notches are only patterned in the CoFeB (soft layer of the MTJ) and not into the Pt underlayer. From the point of view of programming the synapse, the voltage needed to achieve a certain DW position need not be a linear function of position, as this is envisaged to be a pre-calculated analog voltage that is output by the co-processor that implements the learning algorithm.

<table>
<thead>
<tr>
<th>Final Position of the DW</th>
<th>Required ΔPMA (Jm$^{-3}$) over device length</th>
<th>PMA gradient that assists SOT (Jm$^{-3}$/nm)</th>
</tr>
</thead>
<tbody>
<tr>
<td>2$^{nd}$ Notch</td>
<td>$0.2\times10^4$</td>
<td>2.00</td>
</tr>
<tr>
<td>3$^{rd}$ Notch</td>
<td>$1.6\times10^4$</td>
<td>16.00</td>
</tr>
<tr>
<td>4$^{th}$ Notch</td>
<td>$3\times10^4$</td>
<td>30.00</td>
</tr>
<tr>
<td>5$^{th}$ Notch</td>
<td>$3.7\times10^4$</td>
<td>37.00</td>
</tr>
</tbody>
</table>

Table 2. PMA profile in PMA-assisted mode for achieving different positions of the DW. The DW starts at the 1$^{st}$ notch. The second column gives the change in PMA over the entire length of the device required to stop the DW at different notches. The third column shows the gradient in PMA for a 1 $\mu$m long device.

These results show that at this current density the SOT alone cannot drive the DW out of the first notch, but a combination of SOT and PMA gradient can. The PMA gradient reduces the current density required to initiate and sustain the DW motion along the racetrack when compared to the case of SOT only. Because the velocity of the DW increases with the PMA [37], the DW motion is retarded as it moves into the region of lower PMA, helping to arrest the DW at the notches. The synergistic effects of PMA gradient and SOT lead to a lower energy operation. Finally, we confirm through simulation (Fig. 3) that each of the different positions of the DW is achievable deterministically, because at a certain PMA gradient the combined strength of the SOT and PMA gradient is sufficient to move the DW to the desired notch during the SOT ON period. Therefore, for different strengths of the PMA gradient, the DW travels different distances even though the application time of the SOT and PMA gradient is kept constant.
Fig. 3. Micromagnetic model showing the final DW positions in the free layer of the MTJ along with the PMA gradients applied for a synergistic PMA gradient and SOT driven operation of the synaptic weight adjustment. A clear monotonically increasing PMA gradient profile is required to translate the DW from notch 1 (left) to notch 2, 3, 4 or 5. Both current and DW motion are left to right. NOTE: Supplementary Video 1 a, b, c and d shows a movie of the DW dynamics for each of the above PMA gradients.

b. Thermal noise effect at room temperature and scaling issues:

The simulations were repeated with 1000 nm × 100 nm × 1 nm geometry in the presence of thermal noise at 300 K. With thermal noise, the minimum current required to initiate the motion of the DW has a lower value when compared to the zero thermal noise case. Moreover, there is a reduction in the effectiveness of the notch in arresting the motion of the DW in presence of thermal noise. Thus, a slight reduction of current is also required to regain the effectiveness of the notches while keeping it high enough so that DW motion can be initiated. This determined our choice of a current density of \(8.4 \times 10^{12} \text{ A m}^{-2}\) to explore the effect of thermal noise in arresting the DW motion at notch 3 with an assisting PMA gradient.
of 10 Jm\(^{-3}\)/nm. This value of the PMA gradient is chosen between the PMA gradient required for arresting the DW at the 2\(^{nd}\) notch (2 Jm\(^{-3}\)/nm) and the 3\(^{rd}\) notch (16 Jm\(^{-3}\)/nm).

The probability distribution of the final position of the DW is shown in Fig. 4. The DW was most likely to be found in notches 3 or 4, but there was a significant probability of its being located in notches 2 or 5. This is attributed to the relatively small change in energy due to PMA modulation compared to that of thermal energy (\(k_B T= 4.14 \times 10^{-21}\) J). Adjusting the PMA gradient alone did not change the probability distribution enough to localise the DW in a single notch.

To illustrate the energy scales, considering a 10 Jm\(^{-3}\)/nm PMA gradient (i.e. a total PMA modulation of 10 kJm\(^3\) over the length of 1 \(\mu\)m nanowire), this energy change, \(\Delta E = (\Delta \text{PMA}/L) \times \text{notch spacing} \times \text{Volume} = (10 \text{ Jm}^{-3}/\text{nm}) \times 167 \text{ nm} \times 16700 \text{ nm}^3 = 26 \times 10^{-21} \text{ J} \approx \sim 6.5 \text{ k}_B \text{T}.\) Here (\(\Delta \text{PMA}/L\)) is the PMA gradient (\(\Delta \text{PMA}\) over 1 micron length), the volume corresponds to the volume of free layer between two notches, \(k_B\) is the Boltzmann constant and \(T\) is room temperature in Kelvin. This shows that the change in PMA is modest and hence the PMA gradient does not have deterministic control in positioning the DW in the presence of thermal noise. To circumvent this issue, a higher PMA gradient could be used, though this would require a greater strain gradient, or a greater thickness free layer could be used with its PMA derived from bulk effects (e.g. magnetoelastic) instead of interfacial anisotropy. This analysis has not considered edge roughness [38], which can provide additional pinning sites and even remove the need for lithographic patterning of notches.
IV. Energy Efficiency of Deep Neural Networks (DNNs) with Voltage Control of Domain Walls (VC-DW)

While we have discussed the DW dynamics and operation of the non-volatile voltage programmed synapse in detail, Fig. 5 (a) shows the manner in which this device can be adapted to form a hybrid DW-CMOS neuron. The CMOS buffer implements the threshold functionality of a neuron (Fig. 5 a) as well as the ability of the neuron output of one stage to drive inputs to various neurons of the next stage (high fan-out of the CMOS stage) via synapses.

In order to reset the neuron, the SOT clock is used with current flowing in the opposite direction. Thereafter, the SOT clock is used to synchronize the information flow from one state of the DNN to the next. Fig. 5 describes the manner in which the outputs of one set of neurons can be multiplied by the synaptic weights and input to a neuron at the next stage.

**Energy efficiency and area-density of the voltage control DW DNN implementation vs. other implementation schemes**

The energy dissipation in the device can be divided into two parts. One part consists of charging the piezoelectric layer for stress generation, which is essentially the energy lost in charging the capacitor \((1/2)CV^2\), \(C = \text{capacitance due to the PZT layer between the metal contacts, } V = \text{voltage applied}\). The other part is the \(I^2R\) loss of the SOT current through the platinum layer.

For the device modeled in the previous section, the maximum \(\Delta PMA\) was \(0.37 \times 10^5 J m^{-3}\) across the length of the device. The stress required to obtain this may be estimated as \(\sigma = \frac{\Delta PMA}{3/2\lambda}\) where \(\lambda\) is the...
magnetostriction. For CoFeB, with $\lambda \sim 30 \times 10^6$, an unreasonably high stress of $\sim 800$ MPa would be required, but for CoFe with $\lambda \sim 250 \times 10^6$ a stress of order $\sim 100$ MPa can produce the needed $\Delta PMA$. From the Young’s modulus of CoFe of $\sim 2.0 \times 10^5$ MPa, a strain of $\sim 5 \times 10^{-4}$ is required (or more specifically a strain gradient of $5 \times 10^{-4}$ over 1 micron distance). Reference [30] shows that with a 500 µm thick PZT substrate and electrodes of side 600 µm, a strain gradient of $\sim 10^{-3}$ over a distance of 500 µm is feasible with application of 1.5 kV. This suggests that a strain gradient of $\sim 10^{-3}$ ($\sim 5 \times 10^{-4}$ if a single electrode is considered) over 500 nm distance is possible with application of 1.5 V. The effective capacitance, $C= \sim 9\text{fF}$, assuming relative permittivity of 3000. Hence, the energy dissipated is $(1/2)CV^2 \sim 10$ fJ for the electrical control of a scaled DW nanowire device with a footprint of 500 nm $\times$ 50 nm and electrode of foot print 500 nm $\times$ 500 nm.

To calculate the SOT current clocking energy, considering the resistivity of Pt, 100 $\Omega$.nm and charge current density $J_c \sim 4.35 \times 10^{13}$ Am$^{-2}$ through the Pt layer of length 500 nm, width 50 nm and thickness 1 nm for a clocking period of 6 ns, the $I^2R$ loss is $\sim 670$ pJ. This can be further reduced if low damping materials such as iron garnets are used where DW velocities of 0.8 km/s are obtained with current density $\sim 1.2 \times 10^{12}$ Am$^2$ through the Pt layer [39]. Here, over an order of magnitude decrease in current and 10 times decrease in clocking time can result in over 1000 times reduction in SOT write energy to $\sim 50$ fJ. The difficulty will lie in optimizing the edge roughness and geometrical design of the racetrack to provide controllability at such high DW velocities and low Gilbert damping. In summary, this clocked domain wall device concept provides a pathway to realize novel energy efficient DW neuromorphic devices where reprogramming of synaptic weights can be performed at $\sim 60$ fJ per synapse ($\sim 10$ fJ for voltage generated strain and $\sim 50$ fJ for the SOT clocking current) during the learning phase and similarly small $\sim 60$ fJ per neuron during the inference phase of the neural network. Infact, during the inference phase, a neuron implemented with only CMOS devices (not a hybrid DW–CMOS device) would only need $\sim$ few fJ per neuron and the synapses would consume no energy as they are non-volatile.
It is interesting to compare these numbers with alternative implementations of artificial neurons and synapses. The most important benefit of our approach for artificial synapses is the large reduction in energy consumption. The use of strain drastically reduces the energy requirements versus purely spin torque domain wall-based devices [40]. Non-spintronic nanodevices can also provide multilevel synapses, such as oxide-based memristors [41] and phase change memories [23]. Programming such devices requires the physical motion of atoms, in order to create or dissolve conductive filaments (oxide-based memristor) or to crystalize amorphous volumes of chalcogenide materials (phase change memory), which has an inherent energy cost, usually higher than picojoules even in highly scaled devices. On the other hand, these alternative technologies may provide more compact synapses than spintronic ones. Our solution therefore offers an extremely energy efficient approach to potentially implement real time learning-capable systems.

In contrast, the benefits of our approach for implementing artificial neurons is reduction in area (density). As neurons do not require non-volatility, CMOS-based solutions are typically used for neurons and have comparable energy consumption with ours. On the other hand, they typically require multiple transistors and several micrometer square of area [42].

V. Conclusion

The feasibility of an energy efficient voltage-controlled DW implementation of an artificial neuron and synapse was demonstrated using micromagnetic simulations. In this approach, modulation of perpendicular anisotropy with stress (along with SOT) is used to program different synaptic weights as well as to mimic a neuron. Scaling this device to smaller dimensions ~500 nm × 50 nm × 10 nm could result in much lower energy dissipation for implementing synapses as well as high densities for comparable energy dissipation (for implementing neurons) compared to competing approaches. However, to avoid loss of controllability in deterministic positioning of the DW in the presence of thermal noise, careful optimization of material and device geometry are necessary. In summary, this work provides a pathway to the realization of energy efficient voltage controlled artificial neuron networks with real time learning capability and could stimulate more experimental work in this direction.
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